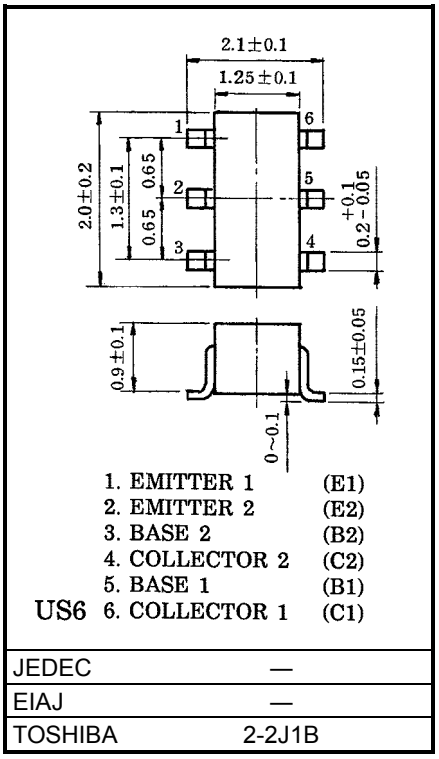
TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

HN2C01FU

Audio Frequency General Purpose Amplifier Applications

Unit: mm

- Small package (dual type)
- High voltage and high current : V_{CEO} = 50V, I_C = 150mA (max)
- High h_{FE} : h_{FE} = 120~400
- Excellent h_{FE} linearity : h_{FE} (I_C = 0.1mA) / (I_C = 2mA) = 0.95 (typ.)



JEDEC	—
EIAJ	—
TOSHIBA	2-2J1B

Weight: 6.8mg

Maximum Ratings (Ta = 25°C) (Q1, Q2 Common)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	150	mA
Base current	I_B	30	mA
Collector power dissipation	P_C*	200	mW
Junction temperature	T_j	125	°C
Storage temperature range	T_{stg}	−55~125	°C

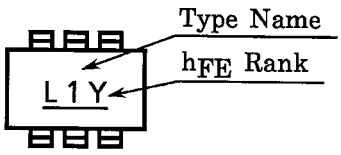
* Total rating

Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

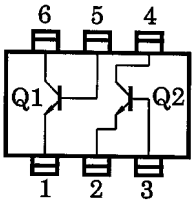
Characteristic	Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	—	V_{CB} = 60V, I_E = 0	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	—	V_{EB} = 5V, I_C = 0	—	—	0.1	μA
DC current gain	$h_{FE\ (Note)}$	—	V_{CE} = 6V, I_C = 2mA	120	—	400	—
Collector-emitter saturation voltage	$V_{CE\ (sat)}$	—	I_C = 100mA, I_B =10mA	—	0.1	0.25	V
Transition frequency	f_T	—	V_{CE} = 10V, I_C = 1mA	80	—	—	MH_Z
Collector output capacitance	C_{ob}	—	V_{CB} = 10V, I_E = 0, f = $1MH_Z$	—	2	3.5	pF

Note: h_{FE} classification
Y(Y): 120~240, GR(G): 200~400
( ) marking symbol

Marking

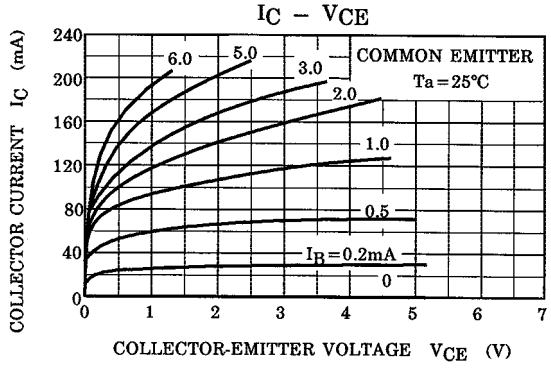


Equivalent Circuit (Top View)

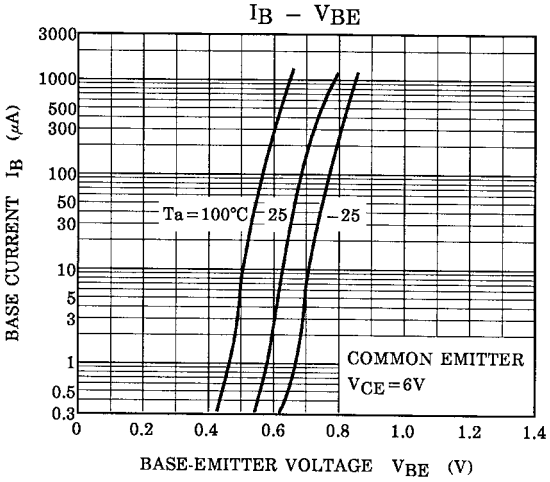


(Q1, Q2 Common)

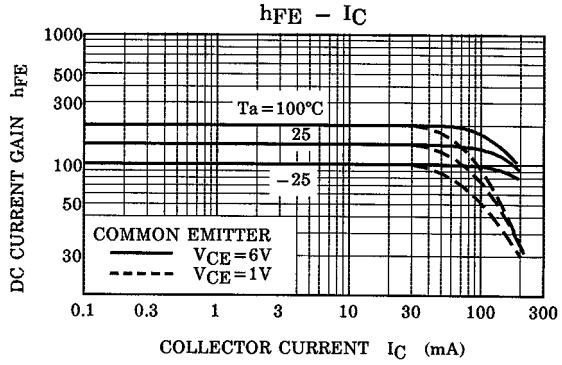
I_C – V_{CE}



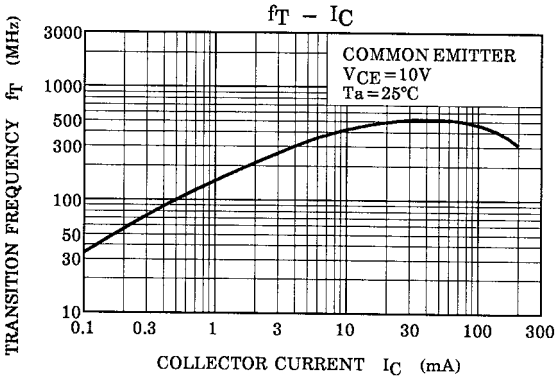
I_B – V_{BE}



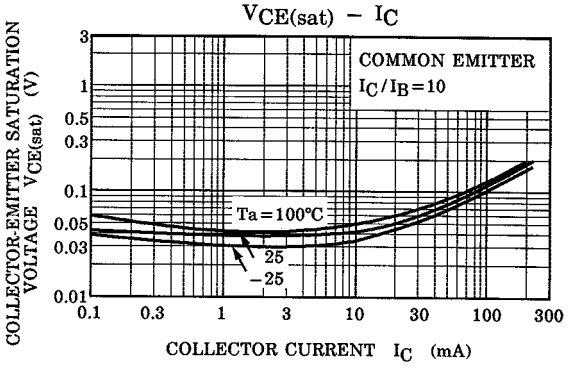
h_{FE} – I_C



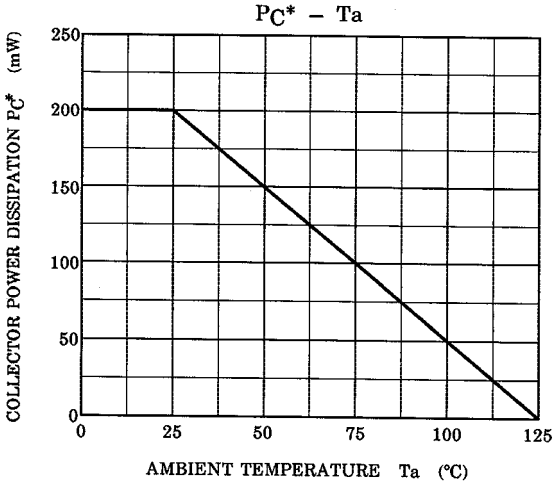
f_T – I_C



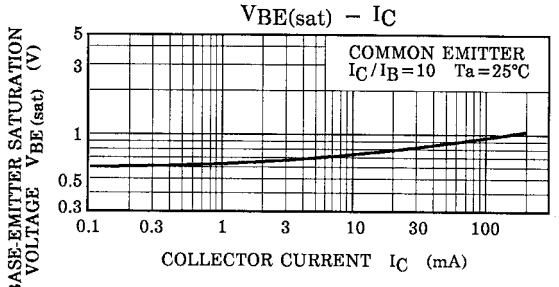
$V_{CE(sat)}$ – I_C



P_C* – Ta



$V_{BE(sat)}$ – I_C



*: Total Rating

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